

DRAM CELL WITH ENHANCED SER IMMUNITY

Abstract of the Disclosure

A memory cell that has first and second fully depleted transfer devices each having a body region and first and second diffused electrodes. The cell has a differential storage capacitor having at least one node abutting and in electrical contact with one of the first and second diffused electrodes of each of the transfer devices. The storage capacitor has a primary capacitance and a plurality of inherent capacitances, wherein the primary capacitance has a capacitive value that is at least approximately five times greater than that of the plurality of inherent capacitances.

